DSS5240T-7 Datasheet

https://www.DiGi-Electronics.com

DiGi Electronics Part Number	DSS5240T-7-DG
Manufacturer	Diodes Incorporated
Manufacturer Product Number	DSS5240T-7
Description	TRANS PNP 40V 2A SOT23-3
Detailed Description	Bipolar (BJT) Transistor PNP 40 V 2 A 100MHz 600 m W Surface Mount SOT-23-3

Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
DSS5240T-7	Diodes Incorporated
Series:	Product Status:
-	Active
Transistor Type:	Current - Collector (Ic) (Max):
PNP	2 A
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ Ib, Ic:
40 V	350mV @ 200mA, 2A
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
100nA (ICBO)	210 @ 1A, 2V
Power - Max:	Frequency - Transition:
600 mW	100MHz
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Surface Mount
Package / Case:	Supplier Device Package:
TO-236-3, SC-59, SOT-23-3	SOT-23-3
Base Product Number:	
DSS5240	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.21.0075	

NOT RECOMMENDED FOR NEW DESIGN
USE ZXTP5240F

Lead-free Green

DSS5240T

40V PNP LOW SATURATION TRANSISTOR IN SOT23

Features

- BV_{CEO} > -40V
- I_C = -2A High Continuous Collector Current
- I_{CM} = -3A Peak Pulse Current
- Low Saturation Voltage -225mV Max @ I_C = -1A
- $R_{CE(SAT)}$ = 90mΩ at -0.5A for a Low Equivalent On-Resistance
- 730mW Power Dissipation
- Complimentary NPN Type: DSS4240T
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/**

Mechanical Data

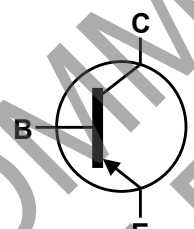
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 e3
- Weight 0.008 grams (Approximate)

Application

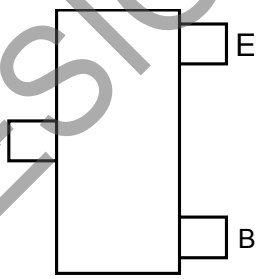
- Gate Driving MOSFETs and IGBTs
- Load Switch
- DC-DC Converters
- Battery Charging

SOT23

Top View



Device Symbol



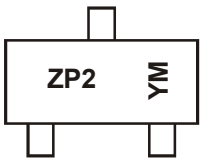
Top View
Pin-Out

Ordering Information (Note 4)

Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DSS5240T-7	NRND (Use ZXTP5240F-7) (Note 5)	ZP2	7	8	3000
DSS5240T-13	NRND (Use ZXTP5240F-7) (Note 5)	ZP2	13	8	10,000

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.
5. NRND – Not recommended for new design.

Marking Information



ZP2 = Product Type Marking Code
YM = Date Code Marking
Y = Year (ex: C = 2015)
M = Month (ex: 9 = September)

Date Code Key

Year	2013	2014	2015	2016	2017	2018	2019	2020	2021	2022	2023
Code	A	B	C	D	E	F	G	H	I	J	K

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

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DSS5240T

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-40	V
Emitter-Base Voltage	V_{EBO}	-5	V
Peak Pulse Collector Current	I_{CM}	-3	A
Continuous Collector Current	I_C	-2	A
Base Current	I_B	-300	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	P_D	730	mW
Power Dissipation (Note 7)	P_D	600	mW
Thermal Resistance, Junction to Ambient Air (Note 6)	$R_{\Theta JA}$	171	°C/W
Thermal Resistance, Junction to Ambient Air (Note 7)	$R_{\Theta JA}$	209	°C/W
Thermal Resistance, Junction to Lead (Note 8)	$R_{\Theta JL}$	75	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge—Human Body Model	ESD HBM	4000	V	3A
Electrostatic Discharge—Machine Model	ESD MM	400	V	C

Notes:
6. For a device mounted with the collector lead on 15mm × 15mm 1oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.
7. Same as Note 6, except the device is mounted on minimum recommended pad layout.
8. Thermal resistance from junction to solder-point (at the end of the collector lead).
9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

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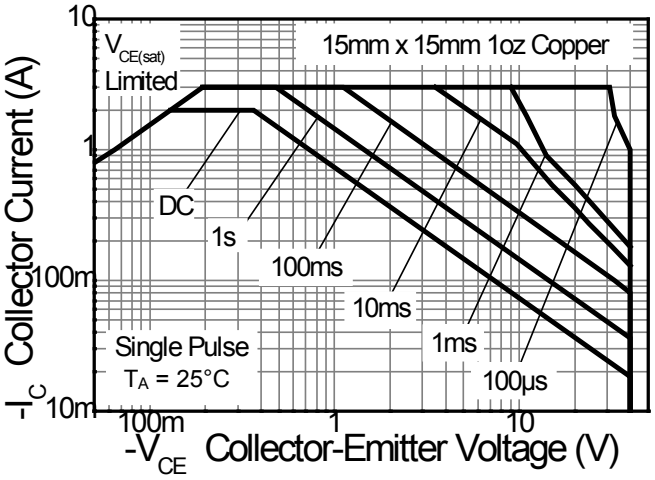
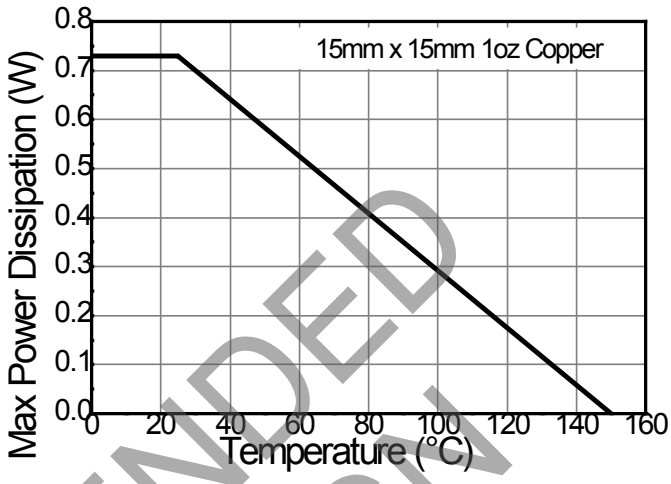
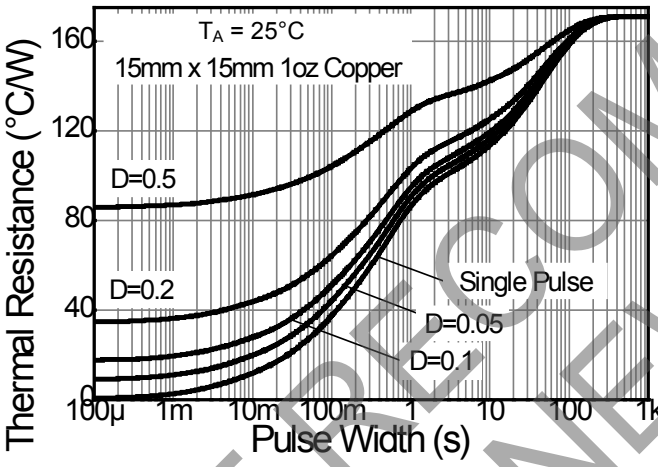
Thermal Characteristics and Derating Information



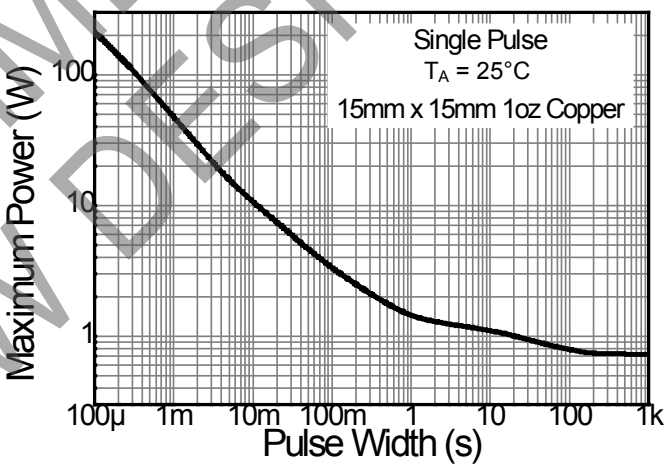
Safe Operating Area



Derating Curve



Transient Thermal Impedance



Pulse Power Dissipation

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Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV_{CBO}	-40	—	—	V	I_C = -100µA
Collector-Emitter Breakdown Voltage (Note 10)	BV_{CEO}	-40	—	—	V	I_C = -10mA
Emitter-Base Breakdown Voltage	BV_{EBO}	-5	—	—	V	I_E = -100µA
Collector-Base Cutoff Current	I_{CBO}	—	—	-100	nA	V_{CB} = -30V, I_E = 0
		—	—	-50	µA	V_{CB} = -30V, I_E = 0, T_A = +150°C
Emitter-Base Cutoff Current	I_{EBO}	—	—	-100	nA	V_{EB} = -4V, I_C = 0
ON CHARACTERISTICS (Note 10)						
DC Current Gain	h_{FE}	300	—	—	—	V_{CE} = -2V, I_C = -0.1A
		260	—	—		V_{CE} = -2V, I_C = -0.5A
		210	—	—		V_{CE} = -2V, I_C = -1A
		100	—	—		V_{CE} = -2V, I_C = -2A
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	—	-100	mV	I_C = -100mA, I_B = -1mA
		—	-45	-110		I_C = -500mA, I_B = -50mA
		—	—	-225		I_C = -750mA, I_B = -15mA
		—	—	-225		I_C = -1A, I_B = -50mA
		—	—	-350		I_C = -2A, I_B = -200mA
Equivalent On-Resistance	$R_{CE(SAT)}$	—	90	220	mΩ	I_C = -500mA, I_B = -50mA
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	—	—	-1.1	V	I_C = -2A, I_B = -200mA
Base-Emitter Turn-on Voltage	$V_{BE(ON)}$	—	—	-0.75	V	V_{CE} = -2V, I_C = -100mA
SMALL SIGNAL CHARACTERISTICS						
Transition Frequency	f_T	100	—	—	MHz	V_{CE} = -10V, I_C = -100mA, f = 100MHz
Output Capacitance	C_{obo}	—	—	28	pF	V_{CB} = -10V, f = 1MHz

Note: 10. Measured under pulsed conditions. Pulse width ≤ 300µs. Duty cycle ≤ 2%.

Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

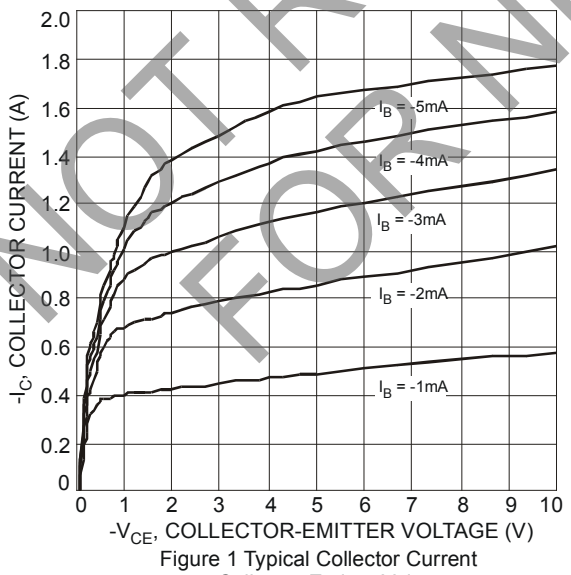

Figure 1 Typical Collector Current vs. Collector-Emitter Voltage

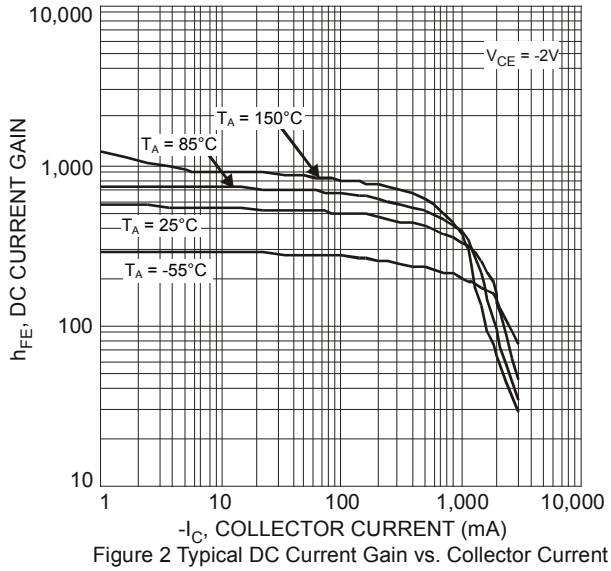

Figure 2 Typical DC Current Gain vs. Collector Current

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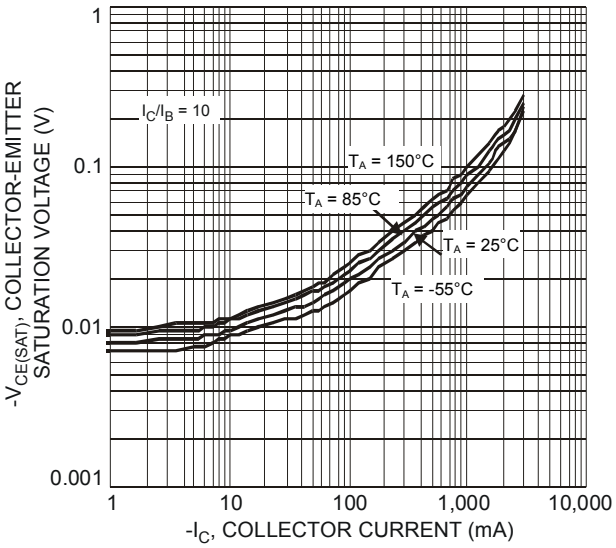

Figure 3 Typical Collector-Emitter Saturation Voltage vs. Collector Current

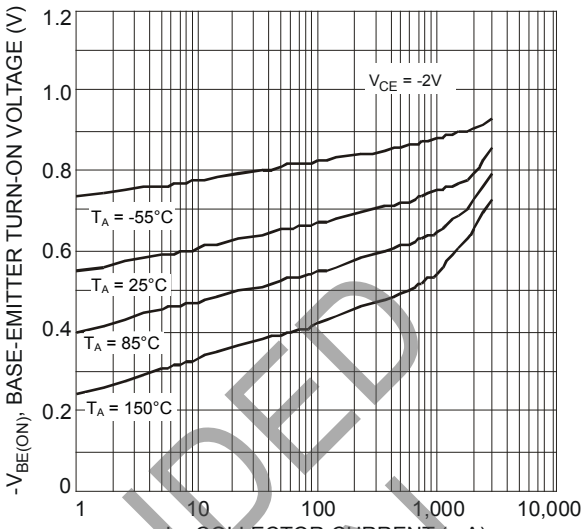

Figure 4 Typical Base-Emitter Turn-On Voltage vs. Collector Current

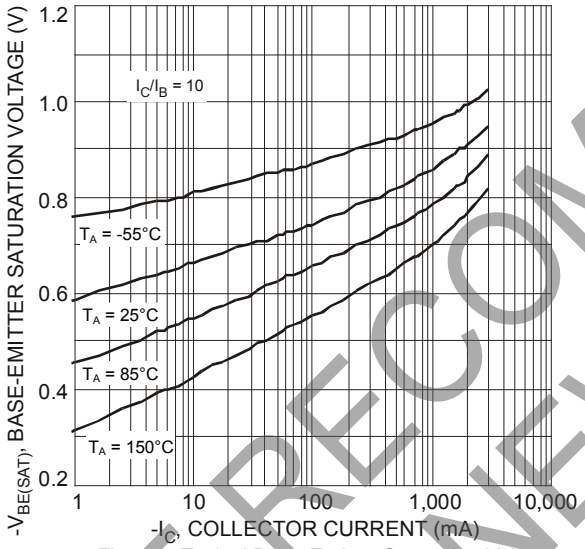

Figure 5 Typical Base-Emitter Saturation Voltage vs. Collector Current

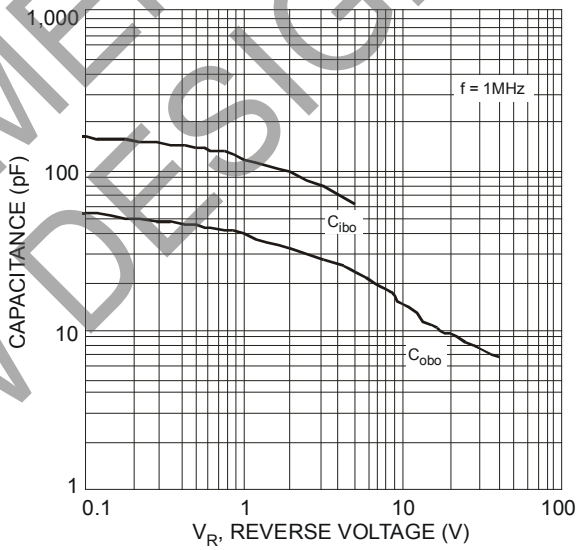

Figure 6 Typical Capacitance Characteristics

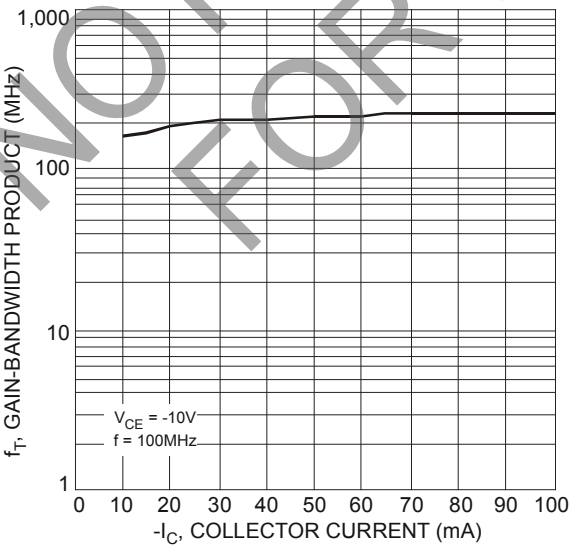

Figure 7 Typical Gain-Bandwidth Product vs. Collector Current

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Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

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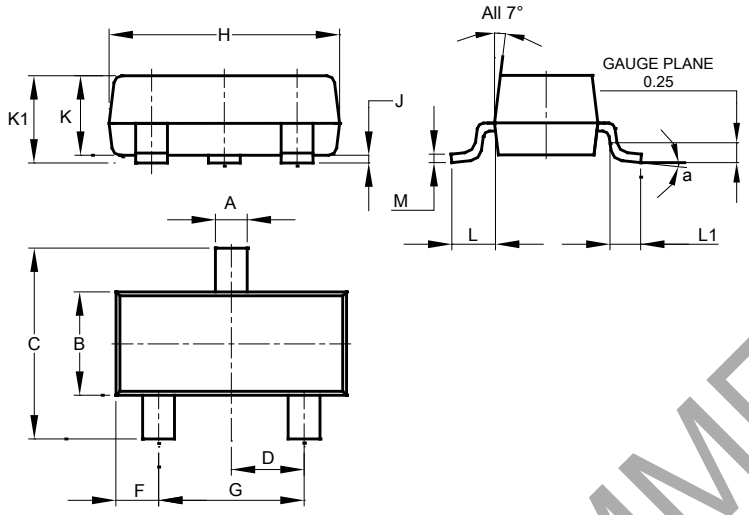
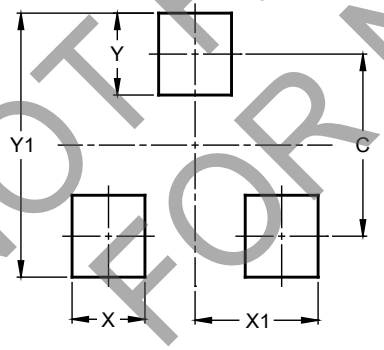


SOT23			
Dim	**Min**	**Max**	**Typ**
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	—
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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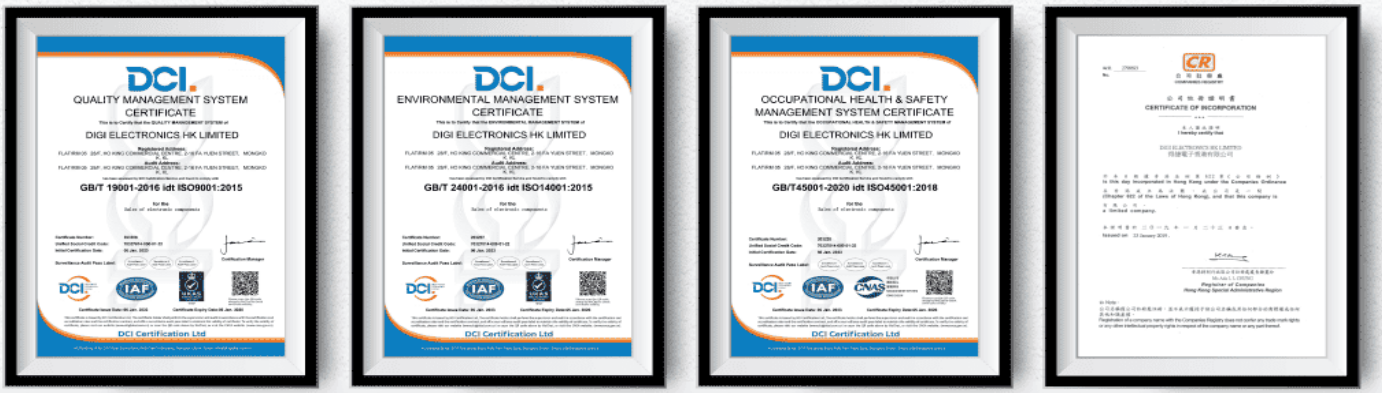

Tel: +00 852-30501935

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